# MCH3477

• High Speed Switching

• Low On-Resistance

• ESD Diode-Protected Gate

• Pb-Free, Halogen Free and RoHS Compliance

Absolute Maximum Ratings at Ta = 25°C

Parameter

**Features** 

• 1.8V Drive

**Specifications** 

Drain to Source Voltage

Gate to Source Voltage

Drain Current (DC)

Power Dissipation

(900mm<sup>2</sup>×0.8mm)

Junction Temperature

Drain Current (Pulse)

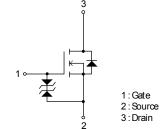
 $PW{\leq}10\mu s,\,duty\,cycle{\leq}1\%$ 





| VDSS | R <sub>DS</sub> (on) Max | ID Max |
|------|--------------------------|--------|
|      | 38 mΩ@4.5V               |        |
| 20V  | 61 mΩ@2.5V               | 4.5A   |
|      | 99 mΩ@1.8V               |        |

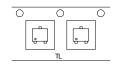




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Packing Type:TL

#### Marking



## Storage Temperature Thermal Resistance Ratings

When mounted on ceramic substrate

| <b>U</b>                          |                 |       |      |
|-----------------------------------|-----------------|-------|------|
| Parameter                         | Symbol          | Value | Unit |
| Junction to Ambient               |                 |       |      |
| When mounted on ceramic substrate | $R_{\theta JA}$ | 125   | °C/W |
| (900mm <sup>2</sup> ×0.8mm)       |                 |       |      |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Value

20

±12

4.5

18

1.0

150

–55 to +150

Symbol

VDSS

VGSS

١D

IDP

 $P_{D}$ 

Тj

Tstg

Unit

۷

v

А

А

W

°C

°C

#### **ORDERING INFORMATION**

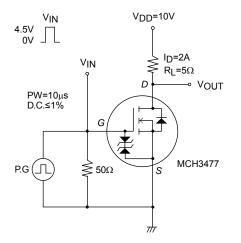
See detailed ordering and shipping information on page 5 of this data sheet.

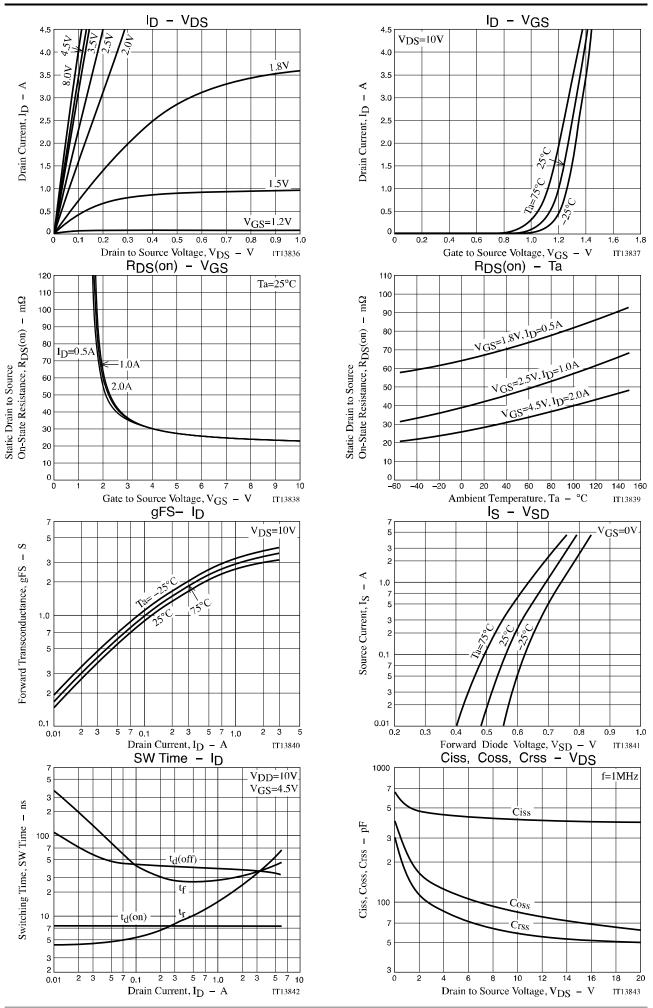
#### **Electrical Characteristics** at Ta = 25°C

| Parameter                                  | Symbol                | Conditions  |     | Value |     |      |
|--|-----------------------|---|-----|-------|-----|------|
| Parameter                                  |                       |   | min | typ   | max | Unit |
| Drain to Source Breakdown Voltage          | V(BR)DSS              | I <sub>D</sub> =1mA, V <sub>GS</sub> =0V                          | 20  |       |     | V    |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                         |     |       | 1   | μA   |
| Gate to Source Leakage Current             | IGSS                  | V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V                         |     |       | ±10 | μA   |
| Gate Threshold Voltage                     | V <sub>GS</sub> (th)  | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA                         | 0.4 |       | 1.3 | V    |
| Forward Transconductance                   | 9FS                   | V <sub>DS</sub> =10V, I <sub>D</sub> =2A                          | 2.0 | 3.4   |     | S    |
|  | R <sub>DS</sub> (on)1 | I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V                         |     | 29    | 38  | mΩ   |
| Static Drain to Source On-State Resistance | R <sub>DS</sub> (on)2 | I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V                         |     | 43    | 61  | mΩ   |
|  | R <sub>DS</sub> (on)3 | I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V                       |     | 69    | 99  | mΩ   |
| Input Capacitance                          | Ciss                  |   |     | 410   |     | pF   |
| Output Capacitance                         | Coss                  | V <sub>DS</sub> =10V, f=1MHz                                      |     | 84    |     | pF   |
| Reverse Transfer Capacitance               | Crss                  |   |     | 59    |     | pF   |
| Turn-ON Delay Time                         | t <sub>d</sub> (on)   |   |     | 7.5   |     | ns   |
| Rise Time                                  | tr                    | See specified Test Circuit  |     | 26    |     | ns   |
| Turn-OFF Delay Time                        | t <sub>d</sub> (off)  |   |     | 38    |     | ns   |
| Fall Time t <sub>f</sub>                   |                       |   |     | 32    |     | ns   |
| Total Gate Charge                          | Qg                    |   |     | 5.1   |     | nC   |
| Gate to Source Charge                      | Qgs                   | V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A |     | 0.7   |     | nC   |
| Gate to Drain "Miller" Charge              | Qgd                   | 1   |     | 1.7   |     | nC   |
| Forward Diode Voltage                      | V <sub>SD</sub>       | I <sub>S</sub> =4.5A, V <sub>GS</sub> =0V                         |     | 0.78  | 1.2 | V    |

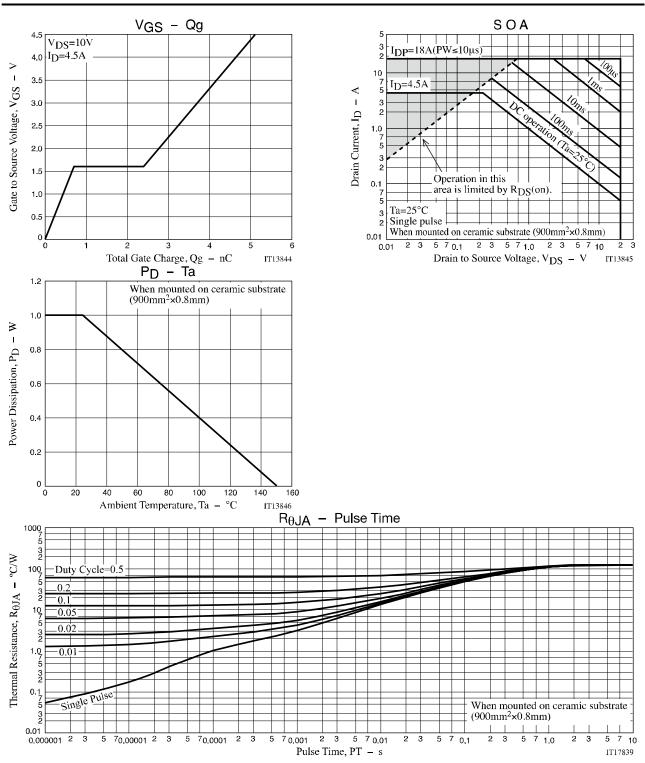
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **Switching Time Test Circuit**





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## **Package Dimensions**

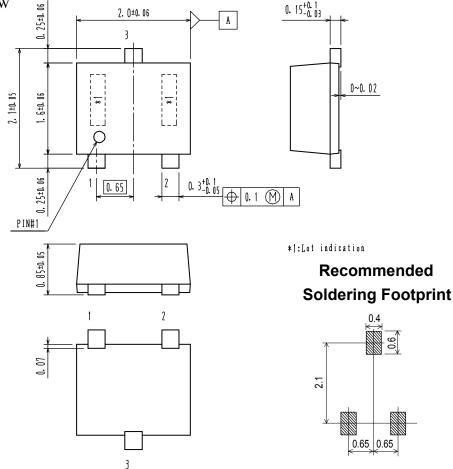
MCH3477-TL-H / MCH3477-TL-W

#### MCPH3

CASE 419AQ ISSUE O

Unit : mm

- 1 : Gate
- 2 : Source
- 3 : Drain



### **ORDERING INFORMATION**

| Device       | Package       | Shipping          | Note             |  |
|--------------|---------------|-------------------|------------------|--|
| MCH3477-TL-H | MCPH3         | 3,000 pcs. / reel | Pb-Free          |  |
| MCH3477-TL-W | SC-70,SOT-323 | 3,000 pcs. / Teel | and Halogen Free |  |

Note on usage : Since the MCH3477 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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